

Mass Spectrometric Investigations of the Evaporation of Crystalline Compounds of the System $\text{Cs}_2\text{O}-\text{Al}_2\text{O}_3-\text{SiO}_2$ *

Part II: The Compounds CsAlSiO_4 and $\text{CsAlSi}_5\text{O}_{12}$

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Dedicated to Professor Dr. H. Hintenberger on his 70th birthday

The evaporation of the synthetic compounds CsAlSiO_4 and $\text{CsAlSi}_5\text{O}_{12}$ was studied by high temperature mass spectrometry. The measurements were carried out under equilibrium conditions with Knudsen cells in the temperature ranges 1242 to 1567 K (CsAlSiO_4) and 1542 to 1803 K ($\text{CsAlSi}_5\text{O}_{12}$). The obtained Cs partial pressures are given by the equations

$$\log p \text{ (Pa)} = -18497/T \text{ (K)} + 11.85 \quad (\text{CsAlSiO}_4) \quad \text{and}$$

$$\log p \text{ (Pa)} = -26974/T \text{ (K)} + 14.6 \quad (\text{CsAlSi}_5\text{O}_{12}) .$$

The probable uncertainty of the vapor pressures is $\pm 43\%$. The following enthalpies of sublimation of Cs (g) were computed:

$$\Delta_{\text{sub}} H_{1405}^\circ (\text{CsAlSiO}_4) = 353.6 \pm 9.8 \text{ kJ mol}^{-1} \quad \text{and}$$

$$\Delta_{\text{sub}} H_{1673}^\circ (\text{CsAlSi}_5\text{O}_{12}) = 516.3 \pm 18 \text{ kJ mol}^{-1} .$$

The Cs partial pressures over CsAlSiO_4 , $\text{CsAlSi}_5\text{O}_{12}$ and $\text{CsAlSi}_2\text{O}_6$ (see part I of this work [1]) are discussed with respect to their consequences for the final storage of high level radioactive waste.

1. Introduction

The volatility of the fission product cesium is one of the significant problems in nuclear technology, applying both its retention in the fuel element during the operating time of the nuclear power plant (see part I of this paper [1]) and its immobilization in glass, glass-ceramic or crystalline products for its final storage [2–4]. Therefore, the evaporation of the compound $\text{CsAlSi}_2\text{O}_6$ was studied in part I [1] of this paper to determine the diminution of the chemical activity of Cs by the formation of this compound.

In addition to the well known compound $\text{CsAlSi}_2\text{O}_6$ there are the two cesium aluminosilicates CsAlSiO_4 and $\text{CsAlSi}_5\text{O}_{12}$ which might also be of interest for a diminution of the chemical activity of Cs. CsAlSiO_4 was for the first time prepared by Barrer and McCallum [5] using hydrothermal crystallization. Solov'eva, Vydrlik and Moroz [6] synthesized this compound from Cs_2CO_3 , silica acid gel and $\text{Al}(\text{OH})_3$ by sintering at tem-

peratures above 1373 K. Klaska and Jarchow [7] also used hydrothermal crystallization for the preparation of CsAlSiO_4 . Finally, Langlet [8] succeeded in preparing this compound by sintering mixtures of CsNO_3 , Al_2O_3 and $\text{SiO}_2 \cdot \text{H}_2\text{O}$ between 773 and 1273 K. Contradictory crystalline structures for CsAlSiO_4 resulted from the aforementioned studies. The structure of CsAlSiO_4 was determined to be cubic [5], tetrahedral [6] and orthorhombic [7].

The compound $\text{CsAlSi}_5\text{O}_{12}$ was recently detected by Ito [9]. He observed $\text{CsAlSi}_5\text{O}_{12}$ single crystals of orthorhombic structure upon slow cooling of a melt containing Ba- and Cs-vanadate.

By preparing samples with different Al_2O_3 -, SiO_2 - and Cs_2O -content we tried to obtain hitherto unknown cesium aluminosilicate compounds [10]. We looked especially for a compound of the composition $\text{Cs}_2\text{O} \cdot \text{Al}_2\text{O}_3 \cdot 6 \text{SiO}_2$ which would represent a homologue of the mineral Albit or potassium feldspar. These efforts were unsuccessful.

No thermodynamic data about the chemical activity of Cs in CsAlSiO_4 and $\text{CsAlSi}_5\text{O}_{12}$ are available. Therefore, these compounds were prepared and their evaporation was studied by high temperature mass spectrometry in order to determine the potentialities of CsAlSiO_4 and $\text{CsAlSi}_5\text{O}_{12}$

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for a retention of Cs in comparison with that of CsAlSi₂O₆.

2. Experimental

The measurements were carried out using the same mass spectrometer Knudsen cell system as it was described in part I [1]. Details are given in [11, 12, 13]. The molybdenum Knudsen cell had a knife edged effusion orifice with a diameter of 0.1 mm. The ions were generated by electron impact with an energy of 22 eV.

The temperatures were measured with an optical pyrometer on the bottom of a black body cavity laterally placed close to and below the bottom of the cylindrical Knudsen cell. A ceramic tube was attached between the inner heat shield and the opening of the black body cavity in the cell in order to avoid differential temperature errors which give rise to large errors for the slope of the vapor pressure curves and hence also for the thermodynamic data derived from it. Without ceramic tube the heat radiation from the cathode which surrounds the Knudsen cell for the heating gets into the black body cavity by reflection on the polished tantalum heat shields and causes a differential temperature error depending on the temperature difference between the cathode and the Knudsen cell. This could be shown by comparing the slope of a measured silver vapor pressure curve with that computed from the data given in the literature [14]. The differential temperature error is, however, only observable at temperatures below about 1300 K since at high temperatures the Knudsen cell is mainly heated by electron bombardment by which the temperature difference between the cell and the cathode is diminished. The aforementioned modification of the temperature measurement has been described in detail in [10].

In order to determine the vaporization of the compounds CsAlSiO₄ and CsAlSi₅O₁₂ samples of stoichiometric composition were prepared using the same preparation procedure with hydrothermal crystal growth as it was employed in part I of this paper [1] to synthesize CsAlSi₂O₆. The samples obtained were checked by X-ray diffraction. Both showed an orthorhombic structure [15]. The volume of the unit cell of CsAlSi₅O₁₂ is approximately twice the amount of the corresponding volume of CsAlSiO₄ [15]. For the CsAlSiO₄ sample all diffrac-

tion lines belong to only one phase. In contrast to that the diffraction pattern of the CsAlSi₅O₁₂ sample showed not only the lines of the orthorhombic CsAlSi₅O₁₂ structure but also those of the compound CsAlSi₂O₆. The coexistence of the two phases is caused by the formation of crystalline nuclei of CsAlSi₂O₆ during the preparation of the sample. The transformation of CsAlSi₂O₆ into CsAlSi₅O₁₂ is difficult on account of the comparatively high stability of CsAlSi₂O₆.

3. Results

During the evaporation of the compounds CsAlSiO₄ and CsAlSi₅O₁₂ the ions Cs⁺, SiO⁺ and Cs²⁺ were observed. The intensities of SiO⁺ and Cs²⁺ are less than 1% in comparison with the Cs⁺ intensity. The ions were identified by their mass and isotopic distribution. Ionisation efficiency measurements of Cs⁺ and the appearance potentials obtained reveal that the Cs⁺ is formed by single ionization.

The Cs partial pressure, p , was determined by using the equation

$$p = E \sigma_{\text{Ag}}/\sigma_{\text{Cs}} \gamma_{\text{Ag}}/\gamma_{\text{Cs}} I_{\text{Cs}} T, \quad (1)$$

where I is the Cs⁺ ion intensity and T the Knudsen cell temperature. The terms $\sigma_{\text{Ag}}/\sigma_{\text{Cs}} = 0.47$ [1] as well as $\gamma_{\text{Ag}}/\gamma_{\text{Cs}} = 1.10$ are the ratios of the ionization cross sections and of the multiplier efficiencies. The $\gamma_{\text{Ag}}/\gamma_{\text{Cs}}$ ratio was estimated by assuming that the multiplier efficiency is proportional to the velocity of the ions impinging on the first dynode of the multiplier. The sensitivity, E , of the Knudsen cell-mass spectrometer system was determined in the same way as it was described in part I of this paper [1] using silver for the pressure calibration.

In order to determine the Cs partial pressures over CsAlSiO₄ and CsAlSi₅O₁₂ two runs were performed for each compound. At the beginning of each measurement all samples showed the same time dependent Cs⁺ ion intensity at constant temperature as it could be observed upon studying the compound CsAlSi₂O₆ [1]. Since the CsAlSiO₄ samples contain only one phase the carrying out of the measurements was analogous to that of the compound CsAlSi₂O₆ [1].

In contrast to that the CsAlSi₅O₁₂ samples contained the two phases CsAlSi₂O₆ and CsAlSi_{2.5}O₁₂. The Cs pressure that could be observed at the

beginning of the measurement of the CsAlSi₅O₁₂ sample after the pressure had become constant at constant temperature, equals that determined over CsAlSi₂O₆ in part I [1] of this paper. After heating the sample for 50 h at 1700 K the vapor pressure decreased at the same temperature and then again became constant. Subsequently, vapor pressure curves were determined by measuring the ion intensities at different temperatures. X-ray diffraction studies of the sample after the evaporation measurement revealed that only the lines of CsAlSi₅O₁₂ could be detected. The loss of the CsAlSi₂O₆ phase is caused by the loss of Cs by effusion through the orifice and by chemical reaction of CsAlSi₂O₆ with the surplus of SiO₂ present in the sample forming CsAlSi₅O₁₂.

The Cs partial pressures obtained over CsAlSiO₄ and CsAlSi₅O₁₂ are shown in Figs. 1 and 2. Logarithmic vapor pressure temperature relationships were obtained by a least squares computation (see Table 1). The enthalpies of sublimation of Cs at the mean temperature of the measurement, T_m , are also tabulated in Table 1. They were computed from the slope of the vapor pressure curves according to the second law method by using the equation

$$\Delta_{\text{sub}} H_{T_m}^\circ = -R \, d \ln p_{\text{Cs}} / d(1/T), \quad (2)$$

where R is the gas constant.

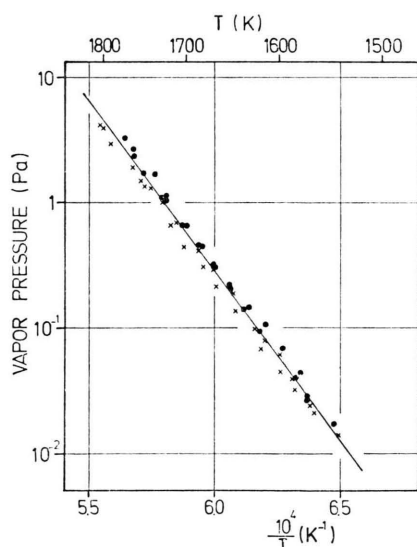


Fig. 1. Cs partial pressures over the compound CsAlSiO₄ (● run 1, × run 2).

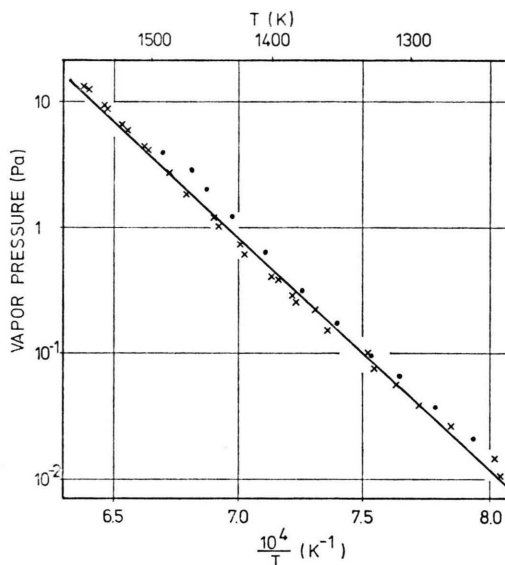


Fig. 2. Cs partial pressures over the compound CsAlSi₅O₁₂ (● run 1, × run 2).

4. Discussion and Conclusions

The errors indicated in Table 1 are random errors resulting from the scatter of the vapor pressure points given in Figs. 1 and 2. The estimated uncertainties of the ratio of the ionization cross sections, the ratio of the multiplier efficiencies, the sensitivity, the temperature and the ion intensities in % are ± 40 , ± 5 , ± 15 , ± 0.5 and ± 5 , respectively. By employing these values a probable uncertainty of $\pm 43\%$ was obtained for the vapor pressure over CsAlSiO₄ and CsAlSi₅O₁₂. The probable uncertainties of the enthalpies of sublimation of Cs are $\pm 9.8 \text{ kJ mol}^{-1}$ (CsAlSiO₄) and $\pm 18 \text{ kJ mol}^{-1}$ (CsAlSi₅O₁₂). They were obtained by assuming the aforementioned absolute temperature error. Additionally, a differential temperature error of $\pm 4 \text{ K}$ at the maximum temperature, and of $\mp 4 \text{ K}$ at the minimum temperature of the various runs carried out for CsAlSiO₄ and CsAlSi₅O₁₂ was taken into account.

Obviously, the vapor pressures and the heats of sublimation obtained in the two different runs for the compound CsAlSiO₄ agree within the accuracy of measurement. The same is true for the data of the two runs obtained on evaporating CsAlSi₅O₁₂.

The Cs vapor pressures over the compound CsAlSiO₄ were also determined by us according to the method of quantitative evaporation [16].

Table 1. Cs vapor pressure and sublimation enthalpy of Cs for CsAlSiO₄ and CsAlSi₅O₁₂.

Compound	Run	Cs pressure (<i>p</i> in Pa, <i>T</i> in K)	<i>p</i> _{Cs} 1450 K (Pa)	Temperature range (K)	<i>T</i> _m (K)	<i>Δ</i> _{sub} <i>H</i> _{<i>T</i>m} (KJ mol ⁻¹)
CsAlSiO ₄	1	$\log p = - (18439 \pm 197)/T + (11.8 \pm 2.2)$	1.21×10^{-1}	1259–1493	1376	351.5 ± 4.2
	2	$\log p = - (18554 \pm 630)/T + (11.9 \pm 2.5)$	1.27×10^{-1}	1242–1567	1405	355.6 ± 12.6
	Average	$\log p = - 18497/T + 11.85$	1.24×10^{-1}	1242–1567	1405	353.6
CsAlSi ₅ O ₁₂	1	$\log p = - (27199 \pm 345)/T + (14.8 \pm 2.3)$	1.10×10^{-4}	1564–1803	1684	512.1 ± 6.3
	2	$\log p = - (26749 \pm 321)/T + (14.4 \pm 2.3)$	8.96×10^{-5}	1542–1769	1656	520.5 ± 6.7
	Average	$\log p = - 26974/T + 14.6$	9.94×10^{-5}	1542–1803	1673	516.3

The vapor pressures determined by quantitative evaporation agree within the accuracy of the measurement with those obtained in this work.

By comparing the Cs partial pressures obtained over the various cesium aluminosilicate compounds at the mean temperature of 1450 K, it follows, that the Cs pressure over CsAlSi₅O₁₂ is by a factor of 22 smaller than that over CsAlSi₂O₆. The compound CsAlSiO₄ has the largest vapor pressure exceeding that of CsAlSi₂O₆ by a factor of 56. Obviously, maximum retention of Cs can be obtained by the formation of CsAlSi₅O₁₂.

Besides the Cs partial pressures, the stability, and leachability of the Cs containing phase are further criteria for the final disposal of solidified liquid waste of high level radioactivity [17, 18]. Considering the stability, crystalline compounds are more suitable than glasses favoured in most countries. There are no data available to compare cesium containing glasses with cesium aluminosilicates regarding the leachability. The demand for crystalline compounds resulting from the stability criterion can be in contradiction to the demand for the minimum vapor pressure since the compound CsAlSi₅O₁₂ has a comparatively high SiO₂ content

thereby favouring the formation of glasses during solidification. The formation of such a glassy phase is influenced by the solidification process [19]. Since until today there are no investigations considering the formation of glasses besides CsAlSi₅O₁₂ at different solidification processes it is impossible to decide whether CsAlSi₅O₁₂ is the most suitable phase to retain Cs during final storage.

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